

KSC2715

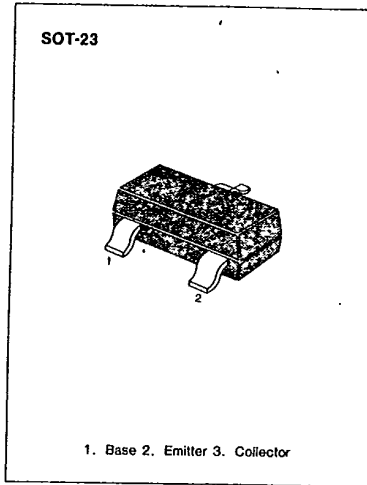
NPN EPITAXIAL SILICON TRANSISTOR

FM RADIO AMP, MIX, CONV OSC, IF AMP

• High Power Gain $G_{pe}=30dB$

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}C$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	50	mA
Collector Dissipation	P_C	150	mW
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55 - 150	$^{\circ}C$



3

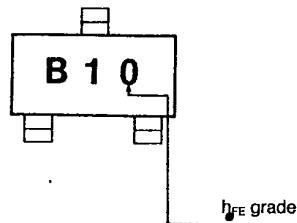
ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=35V, I_E=0$			0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=4V, I_C=0$			1	μA
DC Current Gain	h_{FE}	$V_{CE}=12V, I_C=2mA$	40		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$			0.4	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10mA, I_B=1mA$			1.0	V
Current Gain-Bandwidth Product	f_T	$I_C=1mA, V_{CE}=10V$	100		400	MHz
Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0$ $f=1MHz$		2.	3.2	pF
Power Gain	G_{pe}	$V_{CE}=6V, I_E=-1mA$ $f=10.7MHz$	27	30	33	dB

h_{FE} CLASSIFICATION

Classification	R	O	Y
h_{FE}	40-80	70-140	120-240

Marking

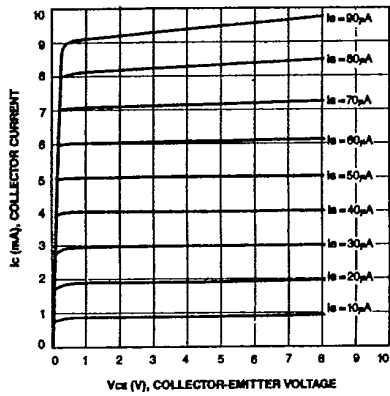


KSC2715

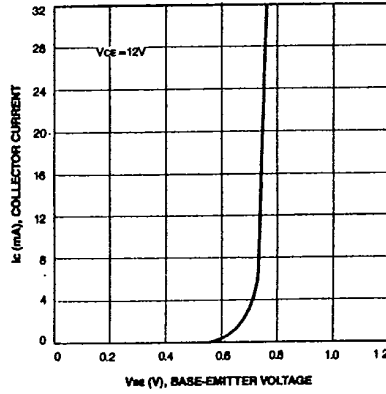
NPN EPITAXIAL SILICON TRANSISTOR

T-31-15

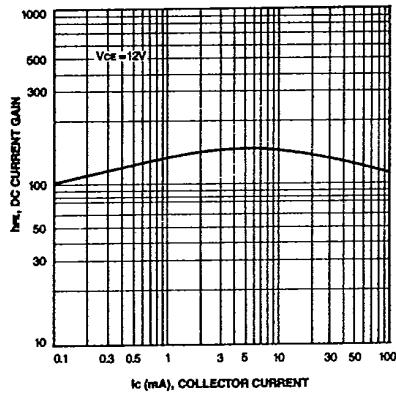
STATIC CHARACTERISTIC



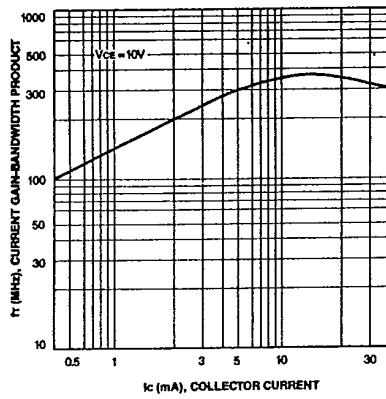
BASE-EMITTER ON VOLTAGE



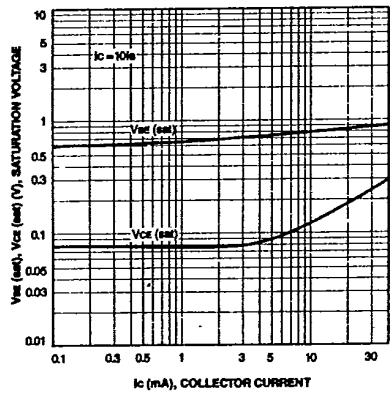
DC CURRENT GAIN



CURRENT GAIN-BANDWIDTH PRODUCT



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE

